WEST Search History

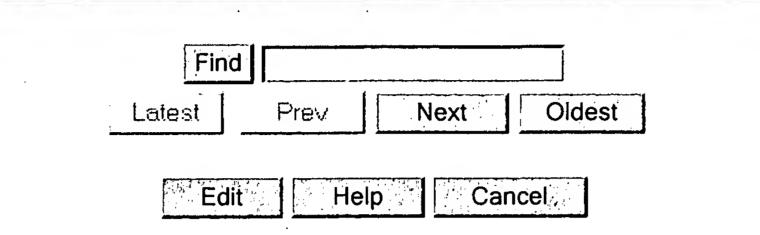| Hide Items | Restore | Clear | Cancel |

DATE: Monday, February 12, 2007

Hide?	Set Name	Query	Hit Count
		DB=PGPB,USPT,USOC; PLUR=YES; OP=ADJ	
☐	L8	L7 and l5	22
☐	L7	134/2,3,19,26,28;216/96,99,108;438/906.ccls.	9637
		DB=EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=ADJ	
☐	L6	L3 and ((clean$3 or wash$3 or etch$3 or oxid$5) same ozon$5) and (hydrofluoric or (hydrogen fluoride) or HF)	2
		DB=PGPB,USPT,USOC; PLUR=YES; OP=ADJ	
☐	L5	L4 and ((clean$3 or wash$3 or etch$3 or oxid$5) same ozon$5) and (hydrofluoric or (hydrogen fluoride) or HF)	500
☐	L4	(wafer or substrate or workpiece or semiconductor) with (anneal$3 or heat$3) with (hydrogen or "H.sib.2")	8650
		DB=EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=ADJ	
☐	L3	(wafer or substrate or workpiece or semiconductor) with (anneal$3 or heat$3) with (hydrogen or "H.sib.2")	4214
		DB=USPT; PLUR=YES; OP=ADJ	
☐	L2	6323140.pn.	1
		DB=PGPB; PLUR=YES; OP=ADJ	
☐	L1	20010053585	1

END OF SEARCH HISTORY

Searches for User *mkornnakov* (Count = 5180)

Queries 5131 through 5180.

Find [   ]

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S #	Updt	Database	Query
S5180	U	PGPB,USPT,USOC	(134/2,3,19,26,28;216/96,99,108;438/906.ccls.)Z and ((wafer or substrate or workpiece or (semiconductor) with (anneal$3 or heat$3) with] (hydrogen or "H.sib.2") and ((clean$3 or wash$3 or etch$3 or oxid$5) same ozon$5) and (hydrofluoric or (hydrogen fluoride) or HF))
S5179	U	PGPB,USPT,USOC	134/2,3,19,26,28;216/96,99,108;438/906.ccls. Z ( ]
S5178	U	EPAB,JPAB,DWPI,TDBD	((wafer or substrate or workpiece or Z semiconductor) with (anneal$3 or heat$3) with ((hydrogen or "H.sib.2")) and ((clean$3 or] wash$3 or etch$3 or oxid$5) same ozon$5) and (hydrofluoric or (hydrogen fluoride) or HF)
S5177	U	PGPB,USPT,USOC	((wafer or substrate or workpiece or Z semiconductor) with (anneal$3 or heat$3) with ((hydrogen or "H.sib.2")) and ((clean$3 or] wash$3 or etch$3 or oxid$5) same ozon$5) and (hydrofluoric or (hydrogen fluoride) or HF)
S5176	U	PGPB,USPT,USOC	(wafer or substrate or workpiece or Z semiconductor) with (anneal$3 or heat$3) with ((hydrogen or "H.sib.2")]
S5175	U	EPAB,JPAB,DWPI,TDBD	(wafer or substrate or workpiece or Z semiconductor) with (anneal$3 or heat$3) with ((hydrogen or "H.sib.2")]
S5174	U	USPT	6323140.pn. Z ( ]
S5173	U	PGPB	20010053585 Z ( ]
S5172	U	PGPB,USPT,USOC	(((wafer or substrate or semiconductor) with Z (anneal$3 or heat$3) with (hydrogen or ("H.sub.2")) same (ozon$4 or "O.sub.3")) and ((hydrofluoric or HF or (hydrogen fluoride))

S5171	U	PGPB,USPT,USOC	(((wafer or substrate or semiconductor) with (anneal$3 or heat$3) with (hydrogen or "H.sub.2")) same (ozon$4 or "O.sub.3")) and (134/2,3,26;438/906.ccls.)	2 ((
S5170	U	PGPB,USPT,USOC	(134/2,3,26;438/906.ccls.) and (((wafer or substrate or semiconductor) with (anneal$3 or heat$3) with (hydrogen or "H.sub.2")) same (ozon$4 or "O.sub.3") and (hydrofluoric or HF or (hydrogen fluoride)))	2 ((
S5169	U	PGPB,USPT,USOC	134/2,3,26;438/906.ccls.	2 ((
S5168	U	PGPB,USPT,USOC	134/2,3,26;438/906.cccls.	2 ((
S5167	U	PGPB,USPT,USOC	(((wafer or substrate or semiconductor) with (anneal$3 or heat$3) with (hydrogen or "H.sub.2")) same (ozon$4 or "O.sub.3")) and (hydrofluoric or HF or (hydrogen fluoride))	2 ((
S5166	U	PGPB,USPT,USOC	((wafer or substrate or semiconductor) with (anneal$3 or heat$3) with (hydrogen or "H.sub.2")) same (ozon$4 or "O.sub.3")	2 ((
S5165	U	EPAB,JPAB,DWPI,TDBD	((wafer or substrate or semiconductor) with (anneal$3 or heat$3) with (hydrogen or "H.sub.2")) same (ozon$4 or "O.sub.3") same (hydrofluoric or HF or (hydrogen fluoride))	2 ((
S5164	U	PGPB,USPT,USOC	((wafer or substrate or semiconductor) with (anneal$3 or heat$3) with (hydrogen or "H.sub.2")) same (ozon$4 or "O.sub.3") same (hydrofluoric or HF or (hydrogen fluoride))	2 ((
S5163	U	PGPB,USPT,USOC	((wafer or substrate or semiconductor) with (anneal$3 or heat$3) with (hydrogen or "H.sub.2")) same ((clean$3 or wash$3 or rins$3 or oxid$7) with (ozon$4 or "O.sub.3") with (hydrofluoric or HF or (hydrogen fluoride)))	2 ((
S5162	U	PGPB,USPT,USOC	((wafer or substrate or semiconductor) with (anneal$3 or heat$3) with (hydrogen or "H.sub.2")) same ((clean$3 or wash$3 or rins$3 or oxid$7) with (ozon$4 or "O.sub.3"))	2 ((
S5161	U	EPAB,JPAB,DWPI,TDBD	((wafer or substrate or semiconductor) with (anneal$3 or heat$3) with (hydrogen or "H.sub.2")) same ((clean$3 or wash$3 or rins$3 or oxid$7) with (ozon$4 or "O.sub.3"))	2 ((
S5160	U	EPAB,JPAB,DWPI,TDBD	((wafer or substrate or semiconductor) with ((anneal$3 or heat$3) adj7 (hydrogen or "H.sub.2")) same ((clean$3 or wash$3 or rins$3 or oxid$7)) with (ozon$4 or "O.sub.3"))	2 ((
S5159	U	PGPB,USPT,USOC	((wafer or substrate or semiconductor) with ((anneal$3 or heat$3) adj7 (hydrogen or	2 (

"H.sub.2")) same ((clean$3 or wash$3 or rins$3 (
or oxid$7)) with (ozon$4 or "O.sub.3"))

S5158	U	PGPB,USPT,USOC	((wafer or substrate or semiconductor) with ((anneal$3 or heat$3) adj7 (hydrogen or "H.sub.2")) same ((clean$3 or wash$3 or rins$3 or oxidiz$5)) with (ozon$4 or "O.sub.3"))
S5157	U	EPAB,JPAB,DWPI	(wafer or substrate or semiconductor) with ((anneal$3 or heat$3) adj7 (hydrogen or "H.sub.2")) with (clean$3 or wash$3 or rins$3) with (ozon$4 or "O.sub.3")
S5156	U	PGPB,USPT,USOC	(wafer or substrate or semiconductor) with ((anneal$3 or heat$3) adj7 (hydrogen or "H.sub.2")) with (clean$3 or wash$3 or rins$3) with (ozon$4 or "O.sub.3")
S5155	U	EPAB,JPAB,DWPI	(wafer or substrate or semiconductor) with ((anneal$3 or heat$3) adj7 (hydrogen or "H.sub.2")) with (clean$3 or wash$3 or rins$3)
S5154	U	PGPB,USPT,USOC	(wafer or substrate or semiconductor) with ((anneal$3 or heat$3) adj7 (hydrogen or "H.sub.2")) with (clean$3 or wash$3 or rins$3)
S5153	U	EPAB,JPAB,DWPI	(wafer or substrate or semiconductor) with ((anneal$3 or heat$3) adj7 (hydrogen or "H.sub.2"))
S5152	U	PGPB,USPT,USOC	(wafer or substrate or semiconductor) with ((anneal$3 or heat$3) adj7 (hydrogen or "H.sub.2"))
S5151	U	PGPB,USPT,USOC	((wafer or substrate) with (anneal$3 or heat$3) with (hydrogen or "h.sub.2") same oxidiz$5) same (hydrofluoric or HF)
S5150	U	PGPB,USPT,USOC	((wafer or substrate) with (anneal$3 or heat$3) with (hydrogen or "h.sub.2") same oxidiz$5) same (hydrofluoric or HF)
S5149	U	PGPB,USPT,USOC	((wafer or substrate) with (anneal$3 or heat$3) with (hydrogen or "h.sub.2")) same oxidiz$5
S5148	U	PGPB,USPT,USOC	((wafer or substrate) with (anneal$3 or heat$3) with (hydrogen or "h.sub.2")) same (ozon$4 with water)
S5147	U	PGPB,USPT,USOC	((wafer or substrate) with (anneal$3 or heat$3) with (hydrogen or "h.sub.2")) same (ozon$4 adj5 water)
S5146	U	PGPB,USPT,USOC	((wafer or substrate) with (anneal$3 or heat$3) with (hydrogen or "h.sub.2")) same (ozon$4 adj3 water)
S5145	U	PGPB,USPT,USOC	(wafer or substrate) with (anneal$3 or heat$3) with (hydrogen or "h.sub.2")
S5144	U	PGPB,USPT,USOC	(wafer or substrate) same ((anneal$3 or heat$3)

			with (hydrogen or "h.sub.2")) same (hydrofluoric or HF) same (ozon$4 adj3 water)	( ]
S5143	U	EPAB,JPAB,DWPI	(wafer or substrate) same ((anneal$3 or heat$3) with (hydrogen or "h.sub.2")) same (hydrofluoric or HF) same (ozon$4 adj3 water)	(( ]
S5142	U	PGPB,USPT,USOC,EPAB,JPAB,DWPI	((toshiba ceramics).as. or izumome-koji$.in. or sakurai-naoaki$.in. or hayamizu-naoya$.in. or yamabe-jyunsei$.in. or ino-takao$.in. or nagahama-hiromi$.in. or kurita-hisatsugu$.in.) and ((wafer or substrate) same ((anneal$3 or heat$3) with (hydrogen or "h.sub.2")) same (hydrofluoric or HF) same (ozon$4 adj3 water))	(( ]
S5141	U	PGPB,USPT,USOC,EPAB,JPAB,DWPI	((toshiba ceramics).as.) or (izumome-koji$.in.) or (sakurai-naoaki$.in.) or (hayamizu-naoya$.in.) or (yamabe-jyunsei$.in.) or (ino-takao$.in.) or (nagahama-hiromi$.in.) or (kurita-hisatsugu$.in.)	(( ]
S5140	U	PGPB,USPT,USOC,EPAB,JPAB,DWPI	(toshiba ceramics).as.	( ]
S5139	U	PGPB,USPT,USOC,EPAB,JPAB,DWPI	izumome-koji$.in.	( ]
S5138	U	PGPB,USPT,USOC,EPAB,JPAB,DWPI	(izumome-koji)$.in.	( ]
S5137	U	PGPB,USPT,USOC,EPAB,JPAB,DWPI	(shibata-izumome)$.in.	( ]
S5136	U	PGPB,USPT,USOC,EPAB,JPAB,DWPI	((shibata-shi)-izumome)$.in.	( ]
S5135	U	PGPB,USPT,USOC,EPAB,JPAB,DWPI	sakurai-naoaki$.in.	( ]
S5134	U	PGPB,USPT,USOC,EPAB,JPAB,DWPI	hayamizu-naoya$.in.	( ]
S5133	U	PGPB,USPT,USOC,EPAB,JPAB,DWPI	yamabe-jyunsei$.in.	( ]
S5132	U	PGPB,USPT,USOC,EPAB,JPAB,DWPI	ino-takao$.in.	( ]
S5131	U	PGPB,USPT,USOC,EPAB,JPAB,DWPI	nagahama-hiromi$.in.	( ]